Amendments to the Claims

1. (currently amended) A method of fabricating a photomask that facilitates accurate measurement of a critical dimension on the photomask, comprising:

projecting a first pattern ~~on~~ onto a substrate in a first area;

projecting at least one test pattern ~~on~~ onto the substrate outside of the first area, wherein said at least one test pattern is representative of the critical dimension on the photomask; and

attaching a pellicle to the substrate, wherein the pellicle covers the first area, but does not cover the at least one test pattern.

2. (previously presented) The method of claim 1, wherein projecting at least one test pattern includes duplicating a portion of the first pattern as the at least one test pattern.

3. (previously presented) The method of claim 2, wherein duplicating a portion of the first pattern as the at least one test pattern includes using optical proximity correction in the at least one test pattern.

4. (previously presented) The method of claim 3, wherein using optical proximity correction includes using shapes selected from the group consisting of serifs, hammerheads and scattering bars.

5. (currently amended) The method of claim 1, wherein projecting the first pattern and projecting the at least one test pattern include projecting the first pattern and the at least one test pattern substantially simultaneously ~~on~~ onto the substrate.

6. (previously presented) The method of claim 1, wherein projecting the first pattern and projecting the at least one test pattern include forming the first pattern and the at least one test pattern under substantially the same conditions.

7. (previously presented) A photomask that facilitates accurate measurement of a critical dimension on the photomask, comprising:

a substrate;

a first pattern formed on the substrate;

at least one test pattern formed on the substrate, wherein said at least one test pattern is representative of the critical dimension on the photomask; and

a pellicle attached to the substrate, wherein the pellicle is not attached over the at least one test pattern.

8. (previously presented) The photomask of claim 7, wherein the at least one test pattern is derived from a portion of the first pattern.

9. (previously presented) The photomask of claim 7, wherein the at least one test pattern includes optical proximity correction.

10. (original) The photomask of claim 9, wherein the optical proximity correction includes shapes selected from the group consisting of serifs, hammerheads and scattering bars.

11. (original) The photomask of claim 7, wherein the photomask is a binary chrome-on-glass mask.

12. (original) The photomask of claim 7, wherein the photomask is a phase shifting mask.

13. (previously presented) A method of monitoring a critical dimension of a photomask including a substrate having a first pattern in a first area, a test pattern in a second area outside of the first area, and a pellicle attached to the substrate which covers the first area but does not cover the second area, wherein a critical dimension of the test pattern is similar in magnitude to a critical dimension of the first pattern, the method comprising:

measuring the critical dimension of the test pattern at a time when the pellicle is attached to the substrate; and

estimating the critical dimension of the first pattern based on the measuring step.

14. (previously presented) The method of claim 1, wherein the at least one test pattern includes patterns typical of the first pattern.

15. (previously presented) The photomask of claim 7, wherein the at least one test pattern includes patterns typical of the first pattern.